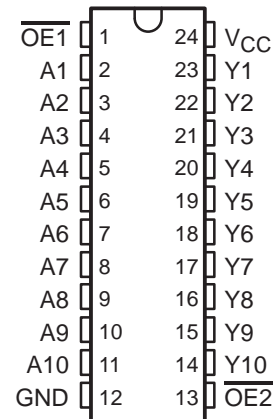


SN74LVC828A 10-BIT BUFFER/DRIVER WITH 3-STATE OUTPUTS

SCAS347E – MARCH 1994 – REVISED JUNE 1998

- **EPIC™** (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at $V_{CC} = 3.3$ V, $T_A = 25^\circ\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at $V_{CC} = 3.3$ V, $T_A = 25^\circ\text{C}$
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model ($C = 200$ pF, $R = 0$)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit buffer/bus driver is designed for 1.65-V to 3.6-V V_{CC} operation.

The SN74LVC828A provides a high-performance bus interface for wide data paths or buses carrying parity.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all ten outputs are in the high-impedance state. The SN74LVC828A provides inverting data at its outputs.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC828A is characterized for operation from -40°C to 85°C .

FUNCTION TABLE

INPUTS			OUTPUT Y
$\overline{OE1}$	$\overline{OE2}$	A	
L	L	L	H
L	L	H	L
H	X	X	Z
X	H	X	Z



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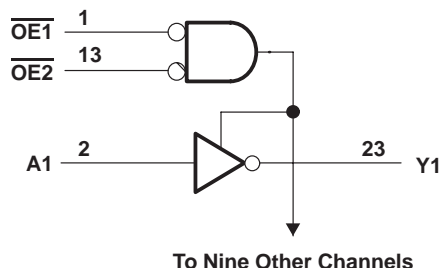
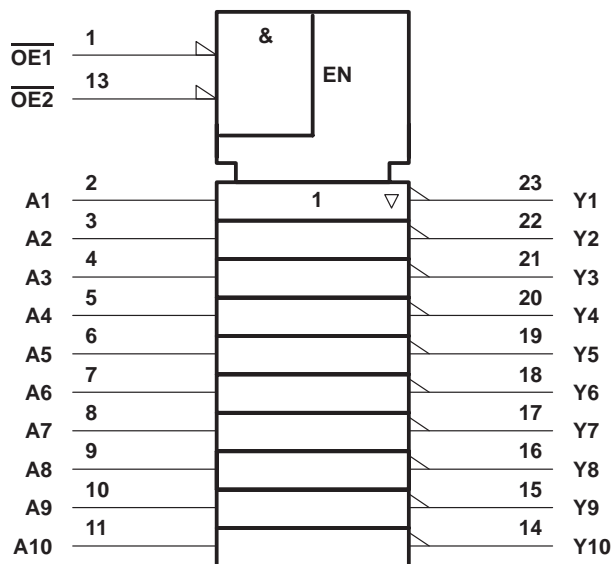


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logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC}	−0.5 V to 6.5 V
Input voltage range, V_I (see Note 1)	−0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1)	−0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2)	−0.5 V to $V_{CC} + 0.5$ V
Input clamp current, I_{IK} ($V_I < 0$)	−50 mA
Output clamp current, I_{OK} ($V_O < 0$)	−50 mA
Continuous output current, I_O	±50 mA
Continuous current through V_{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DB package	104°C/W
DW package	81°C/W
PW package	120°C/W
Storage temperature range, T_{stg}	−65°C to 150°C

NOTES:

1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JEDEC 51.

recommended operating conditions (see Note 4)

		MIN	MAX	UNIT	
V _{CC}	Supply voltage	Operating	1.65	3.6	V
		Data retention only	1.5		
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	1.7		
		V _{CC} = 2.7 V to 3.6 V	2		
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.35 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	0.7		
		V _{CC} = 2.7 V to 3.6 V	0.8		
V _I	Input voltage		0	5.5	V
V _O	Output voltage	High or low state	0	V _{CC}	V
		3 state	0	5.5	
I _{OH}	High-level output current	V _{CC} = 1.65 V	−4		mA
		V _{CC} = 2.3 V	−8		
		V _{CC} = 2.7 V	−12		
		V _{CC} = 3 V	−24		
I _{OL}	Low-level output current	V _{CC} = 1.65 V	4		mA
		V _{CC} = 2.3 V	8		
		V _{CC} = 2.7 V	12		
		V _{CC} = 3 V	24		
Δt/Δv	Input transition rise or fall rate		0	10	ns/V
T _A	Operating free-air temperature		−40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP†	MAX	UNIT
V _{OH}	I _{OH} = –100 µA	1.65 V to 3.6 V	V _{CC} –0.2			V
	I _{OH} = –4 mA	1.65 V	1.2			
	I _{OH} = –8 mA	2.3 V	1.7			
	I _{OH} = –12 mA	2.7 V	2.2			
		3 V	2.4			
	I _{OH} = –24 mA	3 V	2.2			
V _{OL}	I _{OL} = 100 µA	1.65 V to 3.6 V			0.2	V
	I _{OL} = 4 mA	1.65 V			0.45	
	I _{OL} = 8 mA	2.3 V			0.7	
	I _{OL} = 12 mA	2.7 V			0.4	
	I _{OL} = 24 mA	3 V			0.55	
I _I	V _I = 0 to 5.5 V	3.6 V			±5	µA
I _{off}	V _I or V _O = 5.5 V	0			±10	µA
I _{OZ}	V _O = 0 to 5.5 V	3.6 V			±10	µA
I _{CC}	V _I = V _{CC} or GND	3.6 V	I _O = 0		10	µA
	3.6 V ≤ V _I ≤ 5.5 V‡				10	
ΔI _{CC}	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	2.7 V to 3.6 V			500	µA
C _i	V _I = V _{CC} or GND	3.3 V		5		pF
C _o	V _O = V _{CC} or GND	3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

‡ This applies in the disabled state only.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	§	§	§	§	7.1		1	6.7	ns
t _{en}	$\overline{\text{OE}}$	Y	§	§	§	§	8.5		1	7.3	ns
t _{dis}	$\overline{\text{OE}}$	Y	§	§	§	§	7.3		1.8	6.7	ns
t _{sk(o)} ¶										1	ns

§ This information was not available at the time of publication.

¶ Skew between any two outputs of the same package switching in the same direction

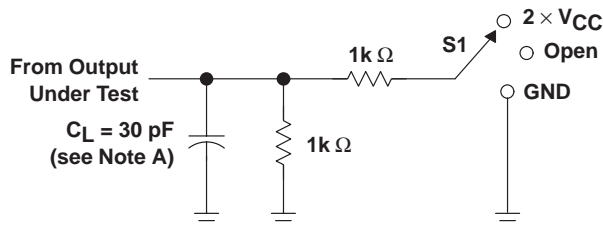
operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V _{CC} = 1.8 V ± 0.15 V	V _{CC} = 2.5 V ± 0.2 V	V _{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	TYP	
C _{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	f = 10 MHz	§	§	24	pF
		Outputs disabled		§	§	7	

§ This information was not available at the time of publication.

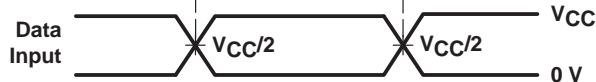
PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$$

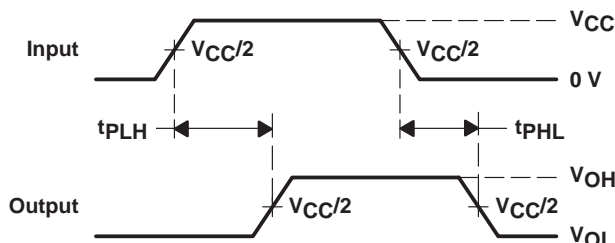


LOAD CIRCUIT

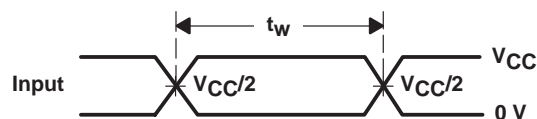
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CC}$
t_{PHZ}/t_{PZH}	Open



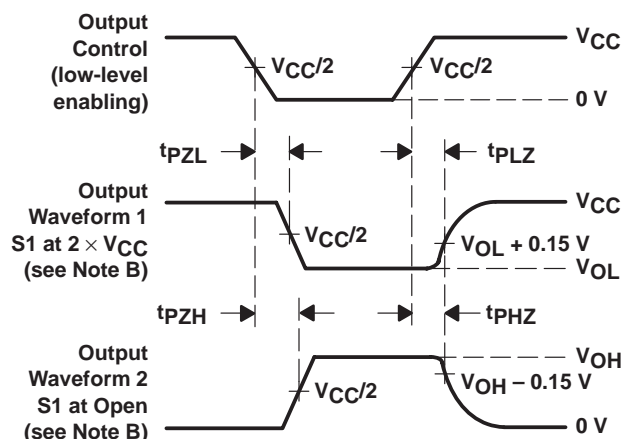
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



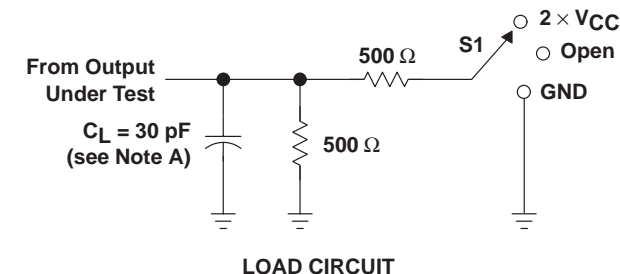
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2 \text{ ns}$, $t_f \leq 2 \text{ ns}$.
 - The outputs are measured one at a time with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .

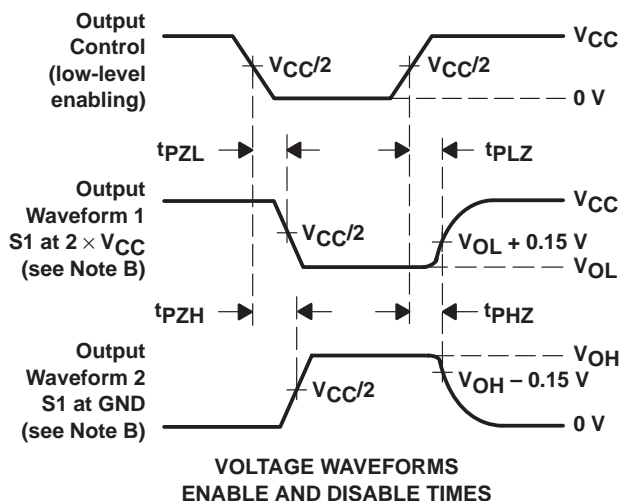
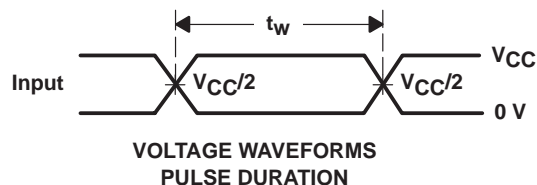
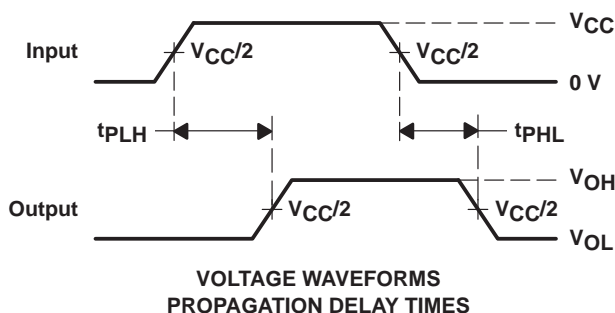
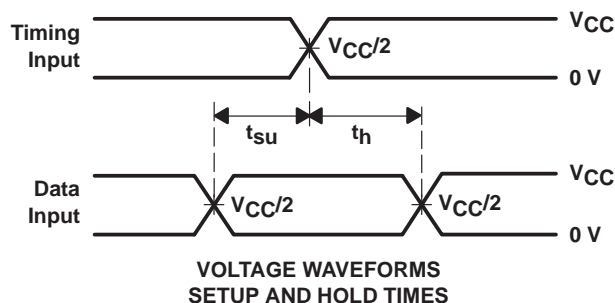
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$$



TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 \times V_{CC}
t_{PHZ}/t_{PZH}	GND

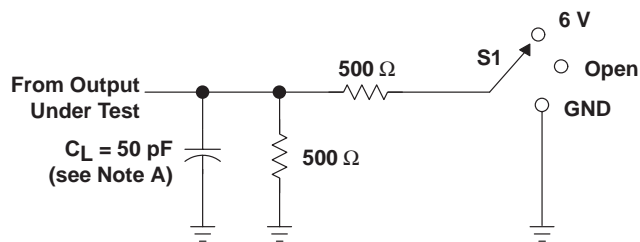


- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2\text{ ns}$, $t_f \leq 2\text{ ns}$.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 2. Load Circuit and Voltage Waveforms

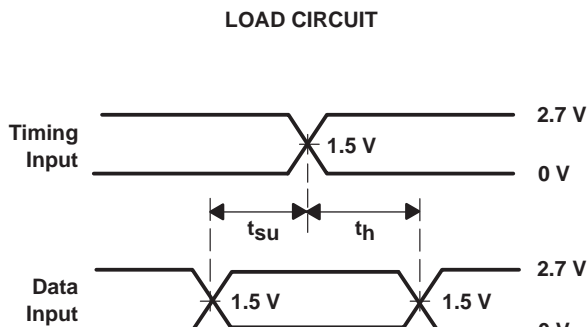
PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 2.7\text{ V AND } 3.3\text{ V} \pm 0.3\text{ V}$

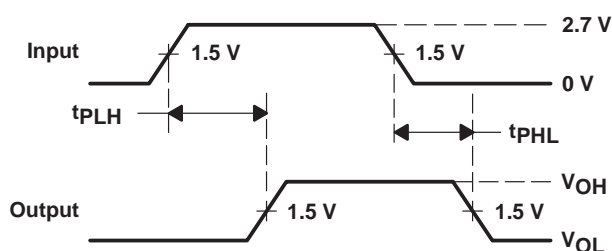


LOAD CIRCUIT

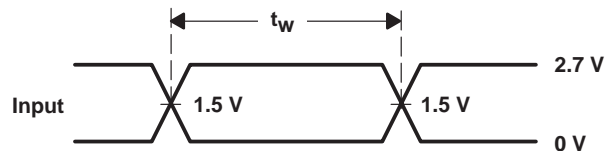
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



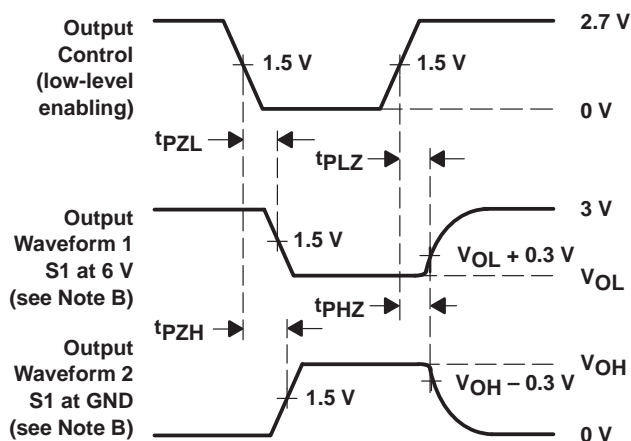
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

- NOTES:
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 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2.5\text{ ns}$, $t_f \leq 2.5\text{ ns}$.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 3. Load Circuit and Voltage Waveforms

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